



A Product Line of Diodes Incorporated



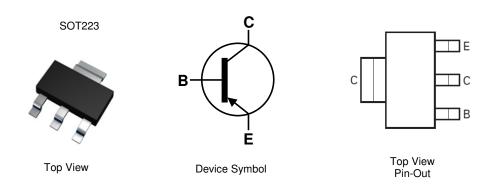
400V PNP HIGH VOLTAGE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -400V
- I_C = -500mA High Continuous Current
- I_{CM} = 1A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < 250mV @ 50mA
- hFE > 40 Specified up to 200mA for High Current Gain Hold Up
- Complementary NPN Type: FZT658
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads;
- Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT758TA	FZT758	7	12	1,000

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

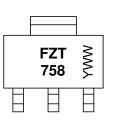
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information

Notes:

SOT223



FZT 758 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-400	V
Collector-Emitter Voltage	V _{CEO}	-400	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	lc	-0.5	А
Peak Pulse Current	I _{CM}	-1	А

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		3.0		
Power Dissipation	(Note 6)	D D	2.0	W	
Fower Dissipation	(Note 7)	PD	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	62.5		
merma Resistance, sunction to Ambient	(Note 7)		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead	(Note 9)	R _{eJL}	12.9		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

still air conditions whilst operating in a steady-state. 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

8. Same as Note 5, except the device is mounted on minimum recommended pad layout.

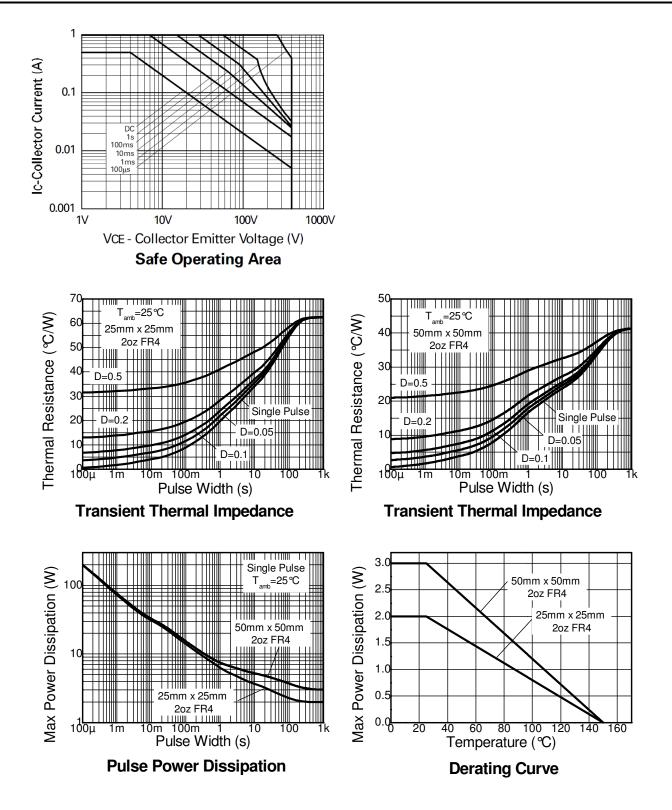
9. Thermal resistance from junction to solder-point (at the end of the collector lead).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





Thermal Characteristics and Derating Information







Electrical Characteristics (@T _A = +25°C, unless otherwise specified.)						
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-400	-	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-400	-	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-	-	V	I _E = -100μA
Collector Cut-Off Current	ICBO	-	-	-100	nA	V _{CB} = -320V
Collector Cut-Off Current	I _{CES}	_	-	-100	nA	V _{CE} = -320V
Emitter Cut-Off Current	I _{EBO}	_	-	-100	nA	$V_{EB} = -4V$
		_	_	-0.30	v	I _C = -20mA, I _B = -1mA
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}			-0.25		$I_{\rm C} = -50 {\rm mA}, I_{\rm B} = -5 {\rm mA}$
				-0.50		I _C = -100mA, I _B = -10mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	-	-0.9	V	I _C = -100mA, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	-	-1.0	V	I _C = -100mA, V _{CE} = -5V
	h _{FE}	50	-	_		$I_{C} = -1mA, V_{CE} = -5V$
DC Current Gain (Note 11)		50	-	-	-	$I_{C} = -100 \text{mA}, V_{CE} = -5 \text{V}$
		40	-	_		$I_{C} = -200 \text{mA}, V_{CE} = -10 \text{V}$
Current Gain-Bandwidth Product (Note 11)	fT	50	-	-	MHz	$V_{CE} = -20V$, $I_C = -20mA$, f = 20MHz
Output Capacitance (Note 11)	C _{obo}	_	-	20	pF	$V_{CB} = -20V, f = 1MHz$
Switching Times	t _{on}	-	140	-		I _C = -100mA, V _{CC} = -100V
Switching Times	t _{off}	_	2,000	-	ns	$I_{B1} = 10mA, I_{B2} = -20mA$

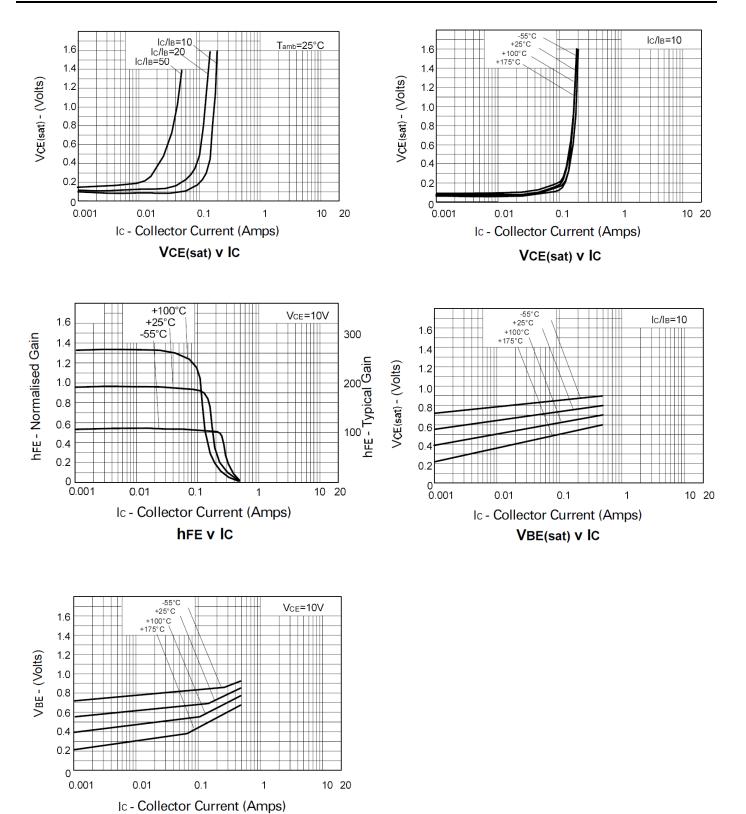
Electrical Characteristics sific

11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%. Note:





Typical Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)



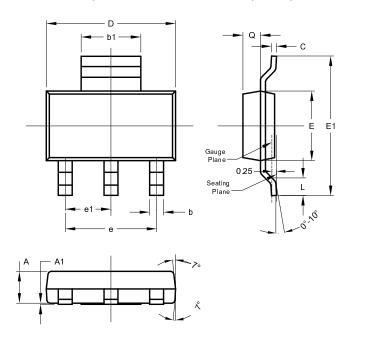
VBE(on) v IC





Package Outline Dimensions

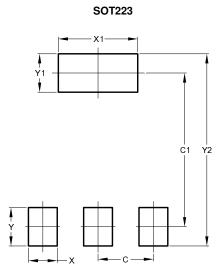
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е			4.60		
e1	_		2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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